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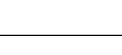
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Fairchild Semiconductor FPN430

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FPN430 FPN430A



PNP Low Saturation Transistor

These devices are designed for high current gain and low saturation voltage with collector currents up to 2.0 A continuous. Sourced from Process PB.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	30	V	
V _{CBO}	Collector-Base Voltage	35	V	
V _{EBO}	Emitter-Base Voltage	5.0	V	
Ic	Collector Current - Continuous	2.0	А	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.

 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		FPN430 / FPN430A		
P _D	Total Device Dissipation	1.0	W	
R _{θJC}	Thermal Resistance, Junction to Case	50	°C/W	
R _{θJA}	Thermal Resistance, Junction to Ambient	125	°C/W	



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PNP Low Saturation Transistor

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAP	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	30		V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	35		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 30 V, I _E = 0 V _{CB} = 30 V, I _E = 0, T _A = 100°C		100 10	nA μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		100	nA

ON CHARACTERISTICS*

h _{FE}	DC Current Gain	$I_C = 100 \text{ mA}, V_{CE} = 2.0 \text{ V}$	430 430A	100 250		
		I _C = 1.0 A, V _{CE} = 2.0 V I _C = 2.0 A, V _{CE} = 2.0 V		60 40		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1.0 A, I _B = 100 mA	430 430A		500 450	mV mV
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 2.0 \text{ A}, I_B = 200 \text{ mA}$ $I_C = 1.0 \text{ A}, I_B = 100 \text{ mA}$			800 1.25	mV V
V _{BE(on)}	Base-Emitter Saturation Voltage	$I_C = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V}$			1.0	V

SMALL SIGNAL CHARACTERISTICS

Cobo	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz		25	pF
F _T	Transition Frequency	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 100 MHz	100		MHz

^{*}Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

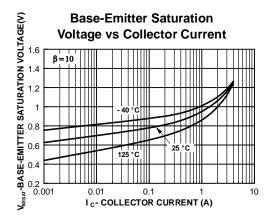
 $\textbf{NOTE:} \ \textbf{All voltages (V)} \ \textbf{and currents (A)} \ \textbf{are negative polarity for PNP transistors}.$

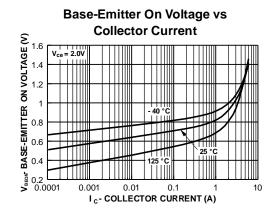


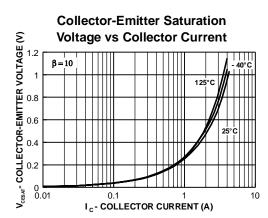
PNP Low Saturation Transistor

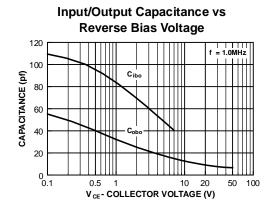
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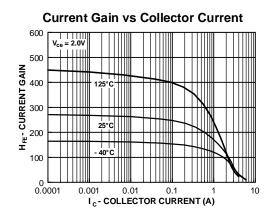
Typical Characteristics

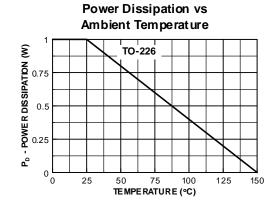














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Datasheet of FPN430 - TRANS PNP 30V 2A TO-226

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Definition of Terms

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Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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